

X Wallart

List of Publications by Year in descending order

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29
papers

1,249
citations

394421

19
h-index

477307

29
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29
all docs

29
docs citations

29
times ranked

1504
citing authors

#	ARTICLE	IF	CITATIONS
1	Kinetic model of element III segregation during molecular beam epitaxy of III-V semiconductor compounds. Applied Physics Letters, 1995, 66, 52-54.	3.3	164
2	High yield of self-catalyzed GaAs nanowire arrays grown on silicon via gallium droplet positioning. Nanotechnology, 2011, 22, 275602.	2.6	146
3	Graphene growth by molecular beam epitaxy using a solid carbon source. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 300-303.	1.8	86
4	Gold-free GaAs/GaAsSb heterostructure nanowires grown on silicon. Applied Physics Letters, 2010, 96, .	3.3	83
5	Graphene growth by molecular beam epitaxy on the carbon-face of SiC. Applied Physics Letters, 2010, 97, .	3.3	80
6	Formation of platinum-based silicide contacts: Kinetics, stoichiometry, and current drive capabilities. Journal of Applied Physics, 2003, 94, 7801.	2.5	76
7	Imaging and controlling electron transport inside a quantum ring. Nature Physics, 2006, 2, 826-830.	16.7	73
8	On the imaging of electron transport in semiconductor quantum structures by scanning-gate microscopy: successes and limitations. Semiconductor Science and Technology, 2011, 26, 064008.	2.0	73
9	Imaging Electron Wave Functions Inside Open Quantum Rings. Physical Review Letters, 2007, 99, 136807.	7.8	65
10	Imaging Coulomb islands in a quantum Hall interferometer. Nature Communications, 2010, 1, 39.	12.8	60
11	Dwell-Time-Limited Coherence in Open Quantum Dots. Physical Review Letters, 2005, 94, 146802.	7.8	47
12	Transport Inefficiency in Branched-Out Mesoscopic Networks: An Analog of the Braess Paradox. Physical Review Letters, 2012, 108, 076802.	7.8	44
13	NanoARPES of twisted bilayer graphene on SiC: absence of velocity renormalization for small angles. Scientific Reports, 2016, 6, 27261.	3.3	28
14	Kinetics and mechanism of low temperature atomic oxygen-assisted oxidation of SiGe layers. Journal of Applied Physics, 1998, 83, 2842-2846.	2.5	27
15	Long dephasing time and high-temperature conductance fluctuations in an open InGaAs quantum dot. Physical Review B, 2002, 66, .	3.2	27
16	X-ray photoemission characterization of interface abruptness and band offset of Ga _{0.5} In _{0.5} P grown on GaAs. Journal of Applied Physics, 1998, 84, 2127-2132.	2.5	26
17	Coherent tunnelling across a quantum point contact in the quantum Hall regime. Scientific Reports, 2013, 3, 1416.	3.3	26
18	High-resolution angle-resolved photoemission spectroscopy study of monolayer and bilayer graphene on the C-face of SiC. Physical Review B, 2013, 88, .	3.2	22

#	ARTICLE	IF	CITATIONS
19	Atomic scale flattening, step formation and graphitization blocking on 6H- and 4H-SiC{0 0 1} surfaces under Si flux. Semiconductor Science and Technology, 2009, 24, 125014.	2.0	20
20	Scanning gate spectroscopy of transport across a quantum Hall nano-island. New Journal of Physics, 2013, 15, 013049.	2.9	19
21	Probing the electronic properties of graphene on C-face SiC down to single domains by nanoresolved photoelectron spectroscopies. Physical Review B, 2015, 92, .	3.2	12
22	Kinetics, stoichiometry, morphology, and current drive capabilities of Ir-based silicides. Journal of Applied Physics, 2007, 102, .	2.5	11
23	Comparative Sb and As segregation at the InP on GaAsSb interface. Applied Physics Letters, 2008, 93, .	3.3	9
24	Plasma assisted oxidation of SiGe layers at 500Å°C: interface characterization. Applied Surface Science, 1996, 104-105, 385-391.	6.1	8
25	Formation of quantum dots in the potential fluctuations of InGaAs heterostructures probed by scanning gate microscopy. Physical Review B, 2015, 91, .	3.2	7
26	Germanium behaviour during the low-temperature plasma-assisted oxidation of SiGe alloys. Surface and Interface Analysis, 1995, 23, 363-366.	1.8	3
27	XPS study of GaInP on GaAs interface. Applied Surface Science, 1998, 123-124, 523-527.	6.1	3
28	Two-dimensional Rutherford-like scattering in ballistic nanodevices. Physical Review B, 2018, 98, .	3.2	3
29	Transmission electron microscopy of iridium silicide contacts for advanced MOSFET structures with Schottky source and drain. Journal of Alloys and Compounds, 2004, 382, 24-28.	5.5	1